



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicants: Yeshwanth Narendar et al.  
Title: METHOD FOR TREATING SEMICONDUCTOR PROCESSING  
COMPONENTS AND COMPONENTS FORMED THEREBY  
App. No.: 10/824,329 Filed: April 14, 2004  
Examiner: Julio J. Maldonado Group Art Unit: 2823  
Customer No.: 34456 Confirmation No.: 5396  
Atty. Dkt. No.: 1035-E4371

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MS RCE  
Commissioner for Patents  
PO Box 1450  
Alexandria, VA 22313-1450

**REQUEST FOR RECONSIDERATION**

Dear Sir:

In response to the Final Office Action mailed September 14, 2006, reconsideration and withdrawal of the rejections contained therein are respectfully requested.

1. Claims 1, 4-9, 14-19 and 21 were rejected under §103 over Thilderkvist et al. in view of Kumar et al. This rejection is respectfully traversed for the following reasons.

As pointed out in Applicants' prior response, the claimed invention is drawn to a semiconductor processing component comprising SiC, having an outer surface portion that consists essentially of CVD-SiC, and has a surface impurity level of not greater than 2X the bulk impurity level (measured at a depth at least 3 microns from the outer surface). The notably reduced surface impurity level may be achieved through processing as described in the present specification, in which an outer target portion of the CVD-SiC coating is removed, generally through an oxidation and etch process. Typically, several oxidation and etch procedures are carried out, thereby removing an